Fearuer

The chips are electrically insulated from bottom plate,2500V AC voltage
Packagde as per intemational standard,Wdided structure,with excdllent
Temperature charecteristics and power cycling capacily
Maximum junction temperature up to 150,Low ronward voltage drop

I_D	200A
V_{DRM}	600-2000V
I_{FSM}	2.1 KA
I^2t	22.1 10^3a^2s

Typical application

DC power supply of appliance and device,input rectifying power supply
of PWM frequency transformer
Excitation source of appliance and device,input rectifying of switching power supply
Charging of soft starting capacitor,Etectric towage and auxillary cuttent
Inversion welder,Current chatging DC power supply

SYMBOL	CHARCTERISTIC	TEST CONDITIONS	T_J (℃)	VALUE		UNIT
				Min	Max	
I_D	Output Current (D.C.)	T_C=100℃	150		200	A
V_{lso}	Insulantion voltage		150	2500		A
V_{RRM}	Repettive peak reverse voltage	V_{DSM}&V_{RSM}=V_{DRM}&$V_{RRM+200V}$	150	600	2000	V
I_{RRM}	Repetitive peak current	V_{RM}=V_{RRM}	150		15	mA
I_{FSM}	Surge on-state current	10ms half sine wave	150		2.1	KA
I^2t	I^2t for fusing coordination	V_R=0.6V_{RRM}			22.1	A^{2S}*10
V_{FO}	Threshold voltage		150		0.8	V
R_F	On-state slop resistance				2.8	mΩ
V_{FM}	Peak on-state voltage	I_{TM}=230A	25		1.35	V
$R_{th(j-c)}$	Thermal impedance node to the shell	180 ° sine wave, single heat sink			0.1	℃/W
$R_{th(c-h)}$	Thermal impedance (shell to powder)	180 ° sine wave, single heat sink			0.07	℃/W
F_M	Mounting force（M5)				4	N-m
	Mounting force（M6)				6	N-m
T_{stq}	Stored temperature			-40	125	℃
W_t	Weight					g
Outline						

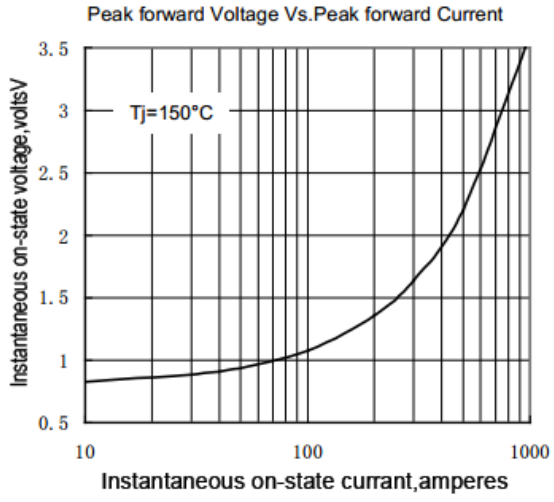


Fig.1

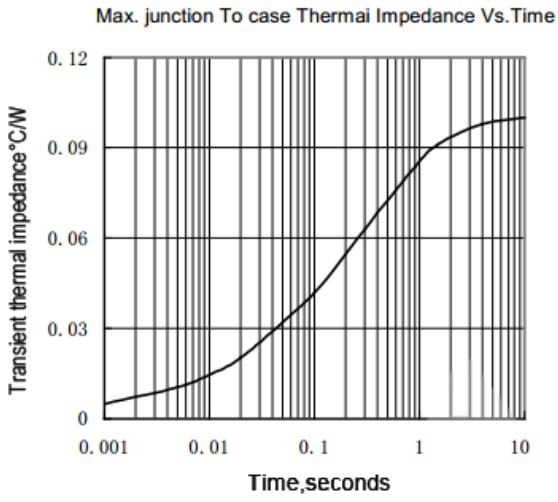


Fig.2

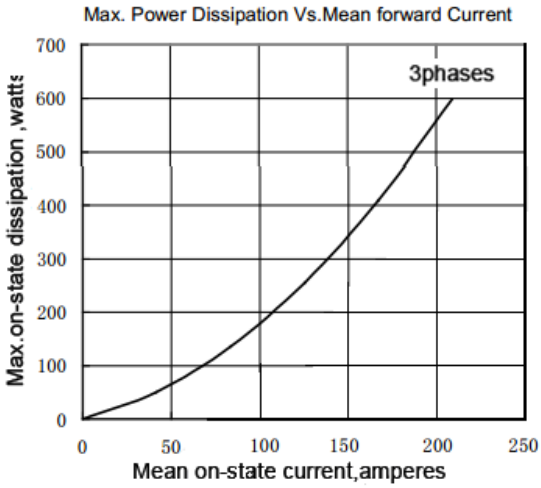


Fig.3

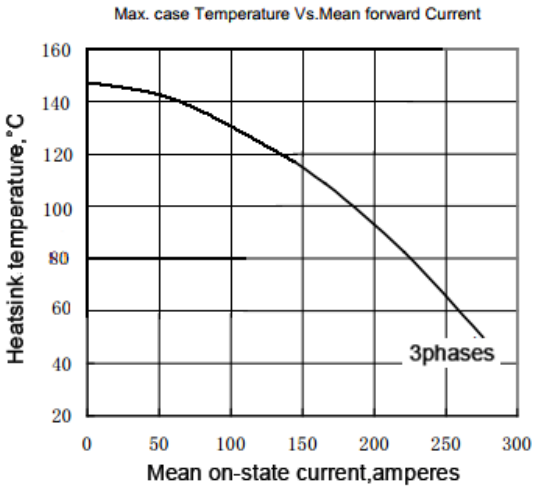


Fig.4

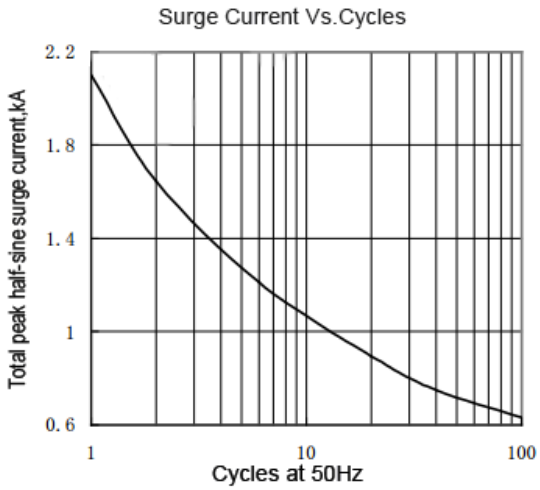


Fig.7

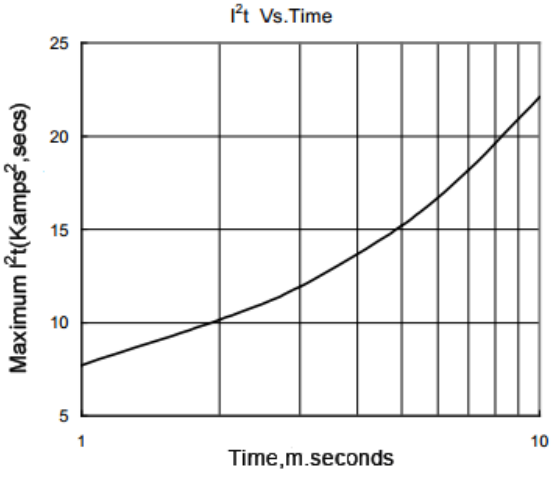
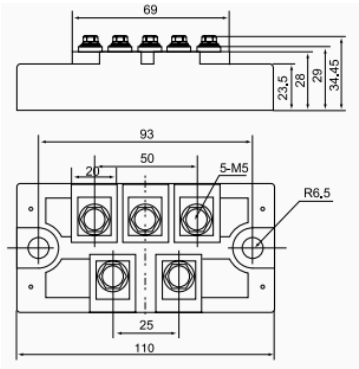
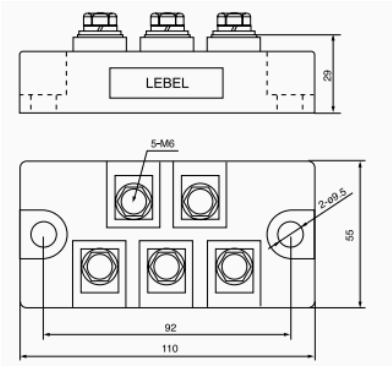


Fig.8

Outline:



1



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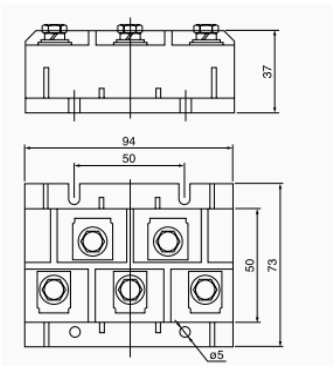

3

Circuit Drawing: